


 U.S. DEPARTMENT OF COMMERCE  
 PATENT AND TRADEMARK OFFICE

 10589892 - GAU: 2829  
 Sheet 1 of 1

## LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

|                                  |                        |                          |
|----------------------------------|------------------------|--------------------------|
| ATTY. DOCKET NO.<br>PKHF-050040  |                        | SERIAL NO.<br>10/589,852 |
| APPLICANT<br>Noboru ICHINOSE     |                        |                          |
| FILING DATE<br>November 27, 2006 | GROUP ART UNIT<br>2829 |                          |

## U.S. PATENT DOCUMENTS

| EXAMINER INITIAL |    | DOCUMENT NO. | DATE       | NAME                                    | CLASS | SUB-CLASS | FILING DATE |
|------------------|----|--------------|------------|---|-------|-----------|-------------|
|                  | AA | 6,030,453    | 02/29/2000 | PASSLACK, et al.                        |       |           |             |
|                  | AB | 2004/0007708 | 01/15/2004 | ICHINOSE, et al. (Previously Submitted) |       |           |             |
|                  | AC |              |            |   |       |           |             |
|                  | AD |              |            |   |       |           |             |
|                  | AE |              |            |   |       |           |             |
|                  | AF |              |            |   |       |           |             |

## FOREIGN PATENT DOCUMENTS

|  |    | DOCUMENT NO. | DATE       | COUNTRY                      | CLASS | SUB-CLASS | TRANSLATION YES NO PART. |
|--|----|--------------|------------|------------------------------|-------|-----------|--------------------------|
|  | AG | 10-289906    | 10/27/1998 | JAPAN (See U.S. 6,030,453)   |       |           | ABS                      |
|  | AH | 10-338522    | 12/22/1998 | JAPAN                        |       |           | ABS                      |
|  | AI | WO 02/12598  | 02/14/2002 | WIPO                         |       |           |                          |
|  | AJ | 2002-093243  | 03/29/2002 | JAPAN (Previously Submitted) |       |           |                          |
|  | AK |              |            |                              |       |           |                          |

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

|    |   |
|----|---|
| AL | Japanese Office Action dated <del>December 2, 2009</del> <sup>2006</sup> with English Translation   |
| AM | Harwig et al., "Electrical Properties of b-Ga2O3 Single Crystals. II," Journal of Solid State Chemistry Vol. 23, pages 205-211, 15 January 1978. (Previously Submitted)   |
| AN | Harwig, T. et al., "Electrical Properties of B-Ga2O3 Single Crystals.", Solid State Communications, 1976, Vol.18, pp. 1223-1225. (Previously Submitted)   |
| AO | Ueda, N. et al., "Synthesis and Control of Conductivity of Ultraviolet Transmitting B-Ga2O3 Single Crystals", in Applied Physics Letters, June 30, 1997, Vol. 70, Issue 26, pages 3561 to 3563. (Previously Submitted)        |
| AP | Tomm, Y. et al., "Floating Zone Growth of B-Ga2O3: A New Window Material for Optoelectronic Device Applications", In: Solar Energy Materials & Solar Cells, February, 2001, Vol. 66, Pages 369 to 374. (Previously Submitted) |
| AQ | Frank J. et al., "Electrical Doping of Gas-Sensitive, Semiconducting Ga2O3 Thin Films", In: Sensors and Actuators B: Chemical, August 1996, Vol. 34, pages 373 to 377. (Previously Submitted)                                 |

|          |                 |                 |            |
|----------|-----------------|-----------------|------------|
| EXAMINER | /Daniel Whalen/ | DATE CONSIDERED | 05/21/2009 |
|----------|-----------------|-----------------|------------|

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.